NSN 5961-01-433-2315

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-433-2315 **Inclosure Material:** Ceramic **Overall Length:** 0.840 inches **Overall Height:** 0.200 inches **Overall Width:** 0.320 inches **Component Name And Quantity:** 4 transistor **Mounting Method: Terminal Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 22.5 drain to substrate voltage all transistor and 22.5 source to substrate voltage all transistor and 15.0 drain to source voltage all transistor **Current Rating Per Characteristic:** 50.00 milliamperes drain current all transistor **Power Rating Per Characteristic:** 640.0 milliwatts total device dissipation all transistor **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Test Data Document:** 19200-12918697 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 16 pin Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0